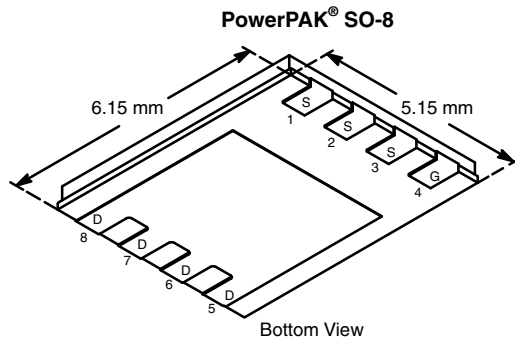


## N-Channel 150 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
150	0.033 at V <sub>GS</sub> = 10 V	35	33 nC



**Ordering Information:**  
SiR838DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

### FEATURES

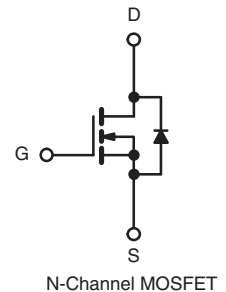
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Primary Side Switch
- Isolated DC/DC Converters



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	150	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	T <sub>C</sub> = 25 °C	35	A
		T <sub>C</sub> = 70 °C	28	
		T <sub>A</sub> = 25 °C	8.3 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	6.6 <sup>b, c</sup>	
Pulsed Drain Current	I <sub>DM</sub>	60		
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	60 <sup>a</sup>	
		T <sub>A</sub> = 25 °C	4.5 <sup>b, c</sup>	
Single Pulse Avalanche Current	I <sub>AS</sub>	30		
Single Pulse Avalanche Energy	E <sub>AS</sub>	45	mJ	
Maximum Power Dissipation	P <sub>D</sub>	T <sub>C</sub> = 25 °C	96	W
		T <sub>C</sub> = 70 °C	62	
		T <sub>A</sub> = 25 °C	5.4 <sup>b, c</sup>	
		T <sub>A</sub> = 70 °C	3.5 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C	
Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, f</sup>	R <sub>thJA</sub>	18	23	°C/W	
Maximum Junction-to-Case (Drain)	R <sub>thJC</sub>	1	1.3		

Notes:

- Package limited
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 65 °C/W.

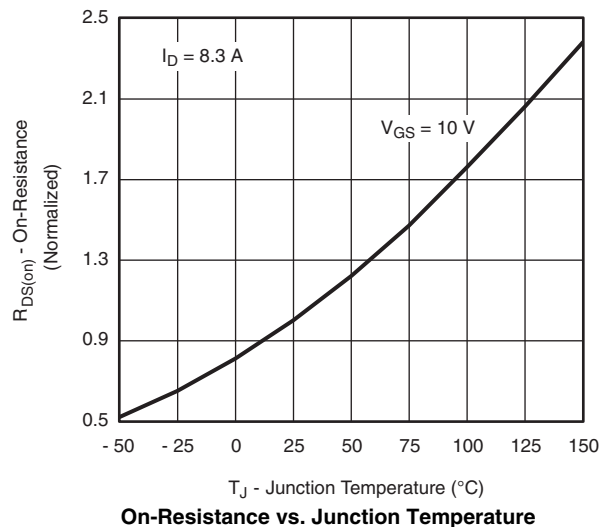
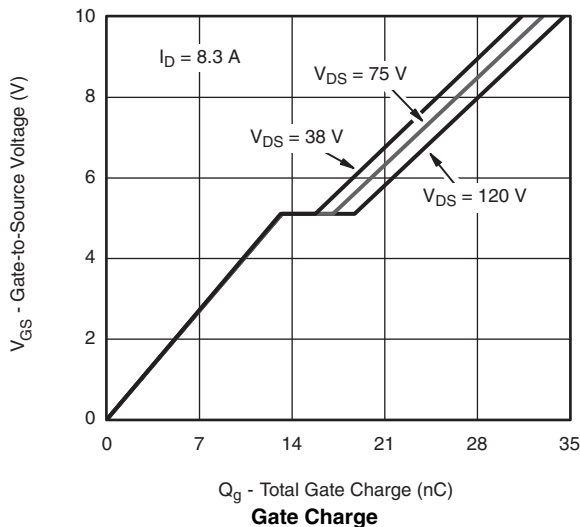
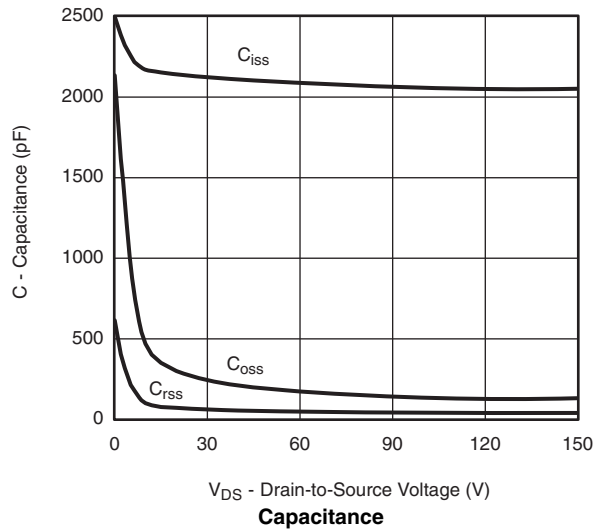
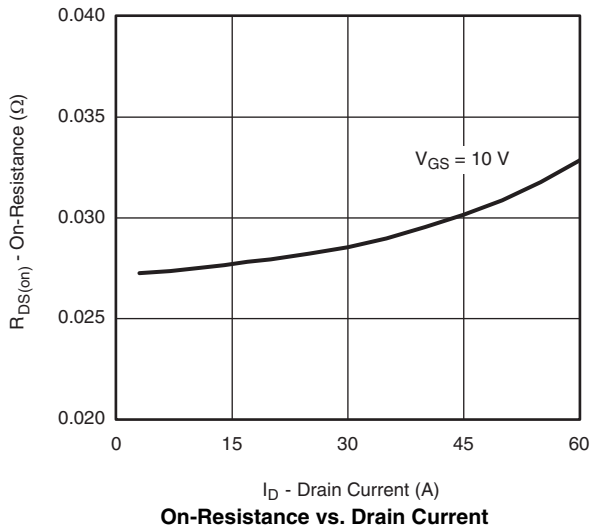
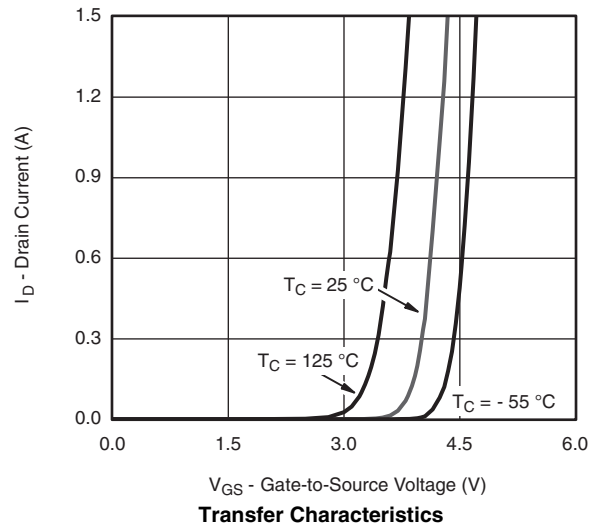
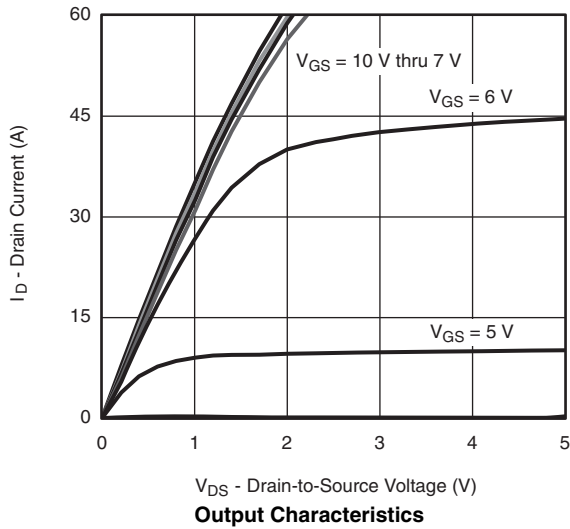
SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	150			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		175		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-9		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2		4	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 150\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8.3\text{ A}$		0.0275	0.0330	$\Omega$
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 8.3\text{ A}$		28		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 75\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		2075		pF
Output Capacitance	$C_{oss}$			155		
Reverse Transfer Capacitance	$C_{rss}$			45		
Total Gate Charge	$Q_g$	$V_{DS} = 75\text{ V}, V_{GS} = 10\text{ V}, I_D = 8.3\text{ A}$		33	50	nC
Gate-Source Charge	$Q_{gs}$			14		
Gate-Drain Charge	$Q_{gd}$			4		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$	0.3	1.4	2.8	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 75\text{ V}, R_L = 11.5\text{ }\Omega$ $I_D \cong 6.6\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		16	25	ns
Rise Time	$t_r$			11	17	
Turn-Off Delay Time	$t_{d(off)}$			23	35	
Fall Time	$t_f$			10	15	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			60	A
Pulse Diode Forward Current	$I_{SM}$				60	
Body Diode Voltage	$V_{SD}$	$I_S = 6.6\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 6.6\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		77	116	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			260	390	nC
Reverse Recovery Fall Time	$t_a$			60		ns
Reverse Recovery Rise Time	$t_b$			17		

Notes:

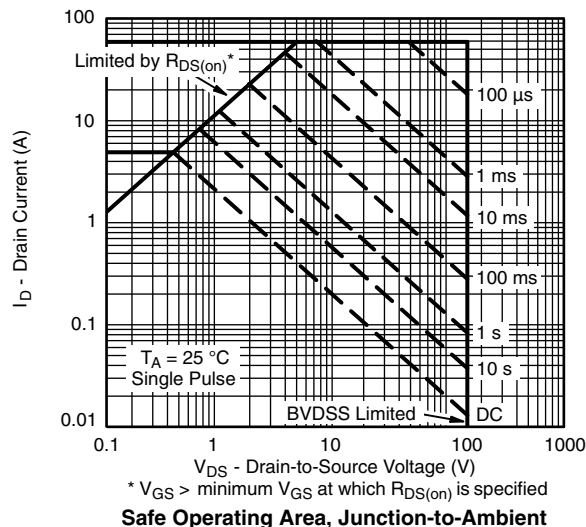
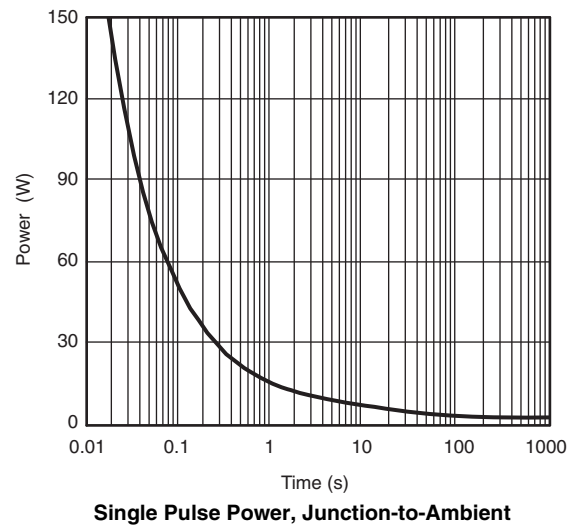
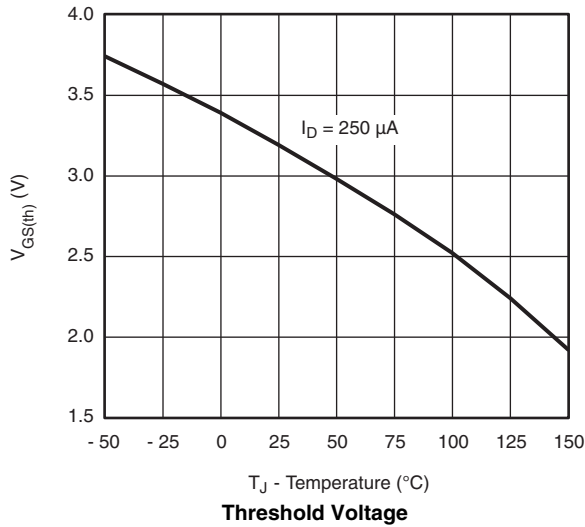
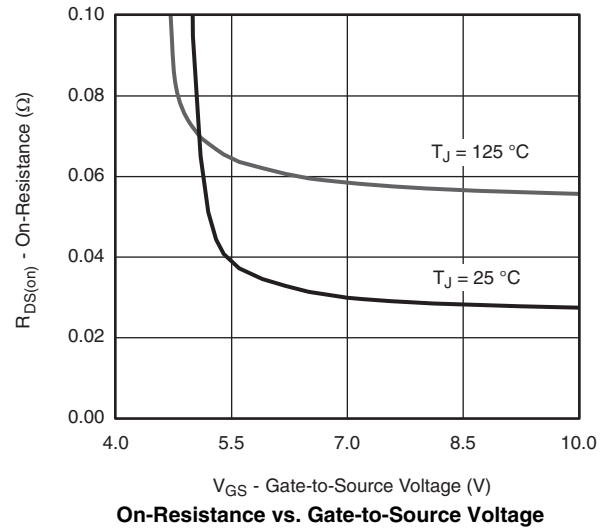
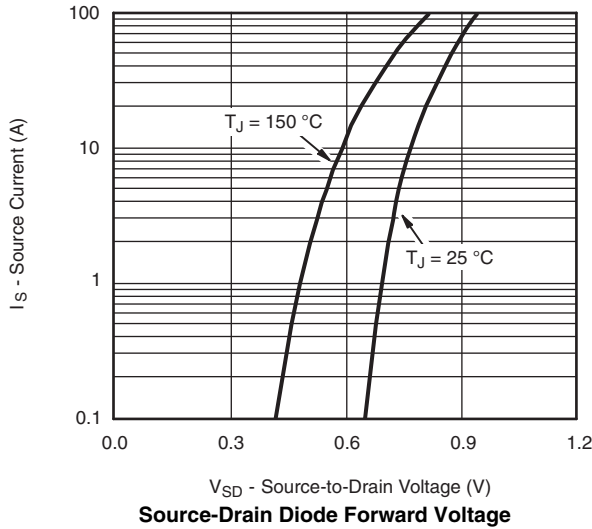
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

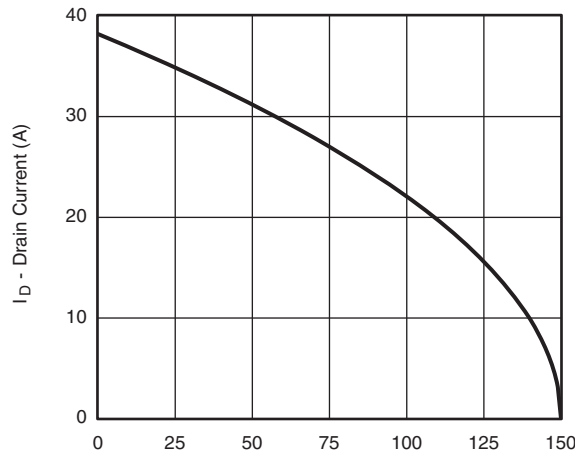
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



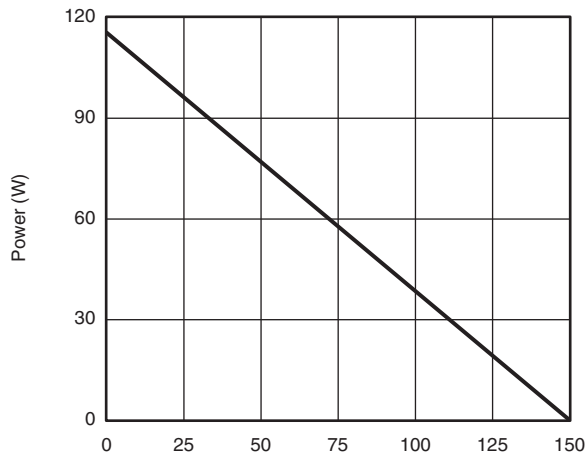
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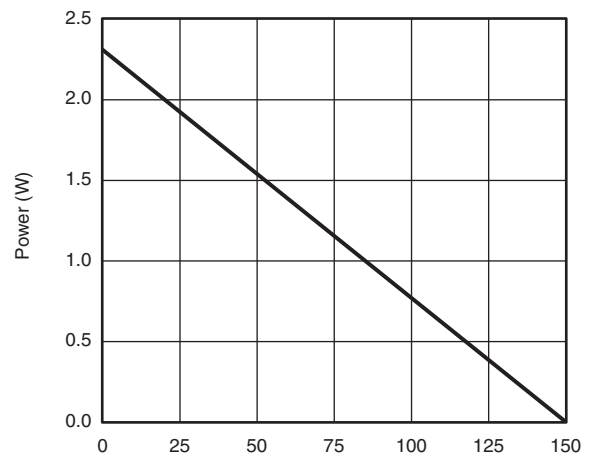
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



$T_C$  - Case Temperature (°C)  
**Current Derating\***



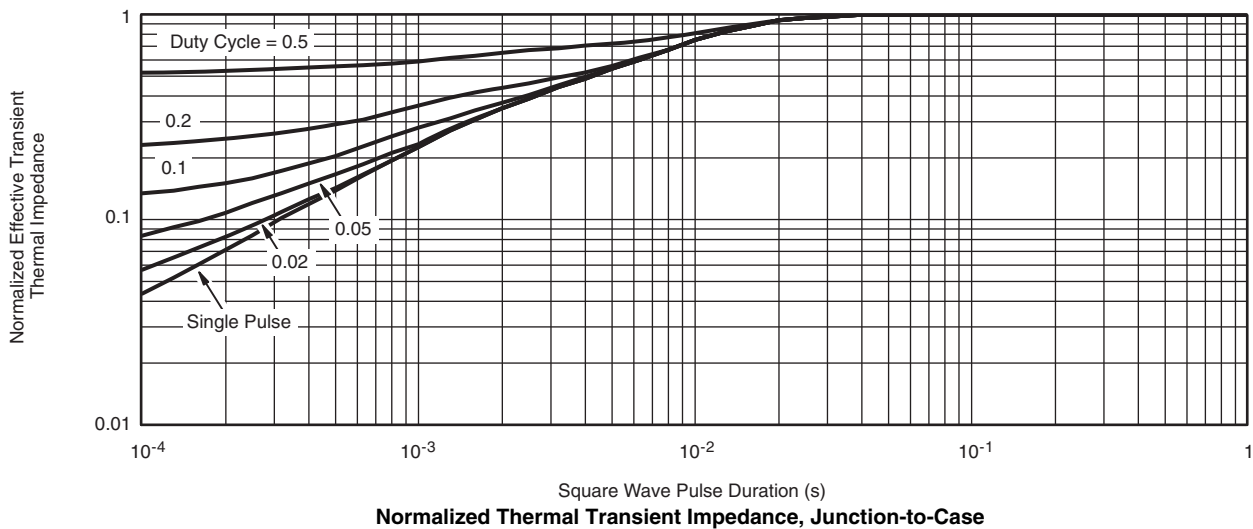
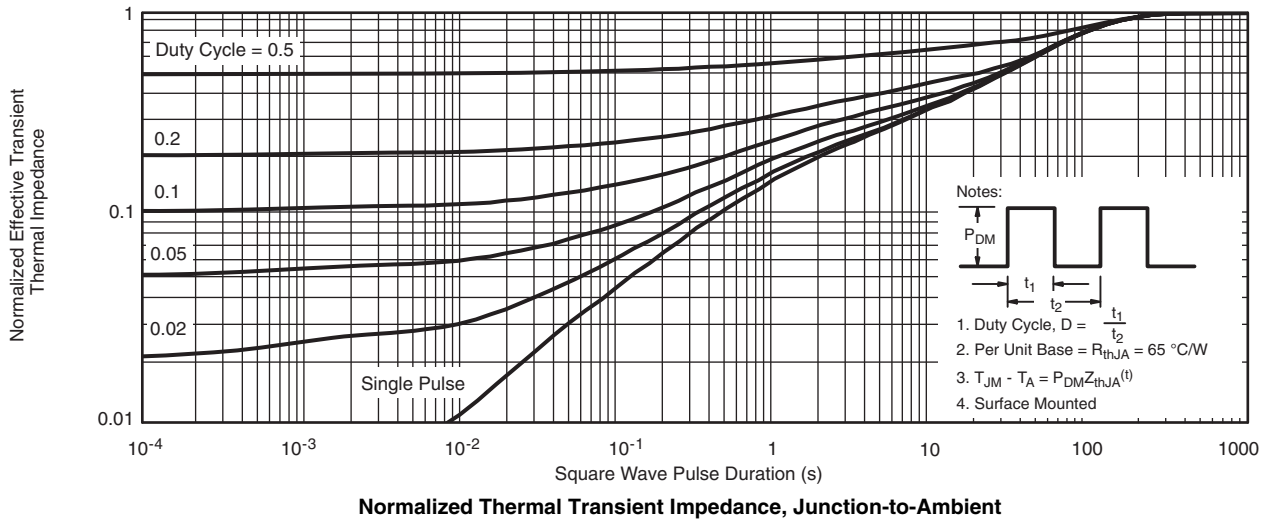
$T_C$  - Case Temperature (°C)  
**Power, Junction-to-Case**



$T_A$  - Ambient Temperature (°C)  
**Power Derating, Junction-to-Ambient**

\* The power dissipation  $P_D$  is based on  $T_{J(max.)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



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